Monte Carlo simulation of single electron device

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Abstract
In the paper, a single-charge tunneling simulator, the Monte Carlo simulator of single Electron Tunneling Device using Orthodox theory and Monte Carlo method is introduced. It simulates the propagation of electrons through a network consisting of small tunnel junctions, capacitors and ideal voltage sources. The simulation of the SET (single electron transistor) which is comprised of single Columb island and multi-islands are done using the simulator.

References

Description of original document (in Chinese)
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